



E.O.T.G.
#16/Amde
2403
PATENT
Attorney Docket No. 400762/AOYAMA
C. Moore

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

SUZUKI et al.

Application No. 09/613,749

Art Unit: 2814

Filed: July 11, 2000

Examiner: A. Rao

For: FIELD EFFECT TRANSISTOR
STRUCTURE WITH BENT GATE

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TECHNOLOGY CENTER 2800
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RESPONSE TO OFFICE ACTION

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated October 4, 2002, please enter the following amendments and consider the following remarks.

AMENDMENTS

IN THE CLAIMS:

Replace the indicated claim with:

18. (Amended) A semiconductor device comprising:
a compound semiconductor substrate having a first surface and a second surface, the compound semiconductor substrate being electrically isotropic in two mutually orthogonal directions;
first, second, and third active regions on the first surface of the substrate, the first and second active regions being separated by a first insulating region and the second and third active regions being separated by a second insulating region;
a first semiconductor element including
first, second, and third channel regions serially connected, adjacent channel regions having width directions essentially perpendicular to each other,
a first source electrode and a first drain electrode, adjacent to the first, second, and third channel regions and opposing each other with the first, second, and third channel regions therebetween, and in ohmic contact with the first, second, and third active regions, and